

# D4SBS4

40V 4A

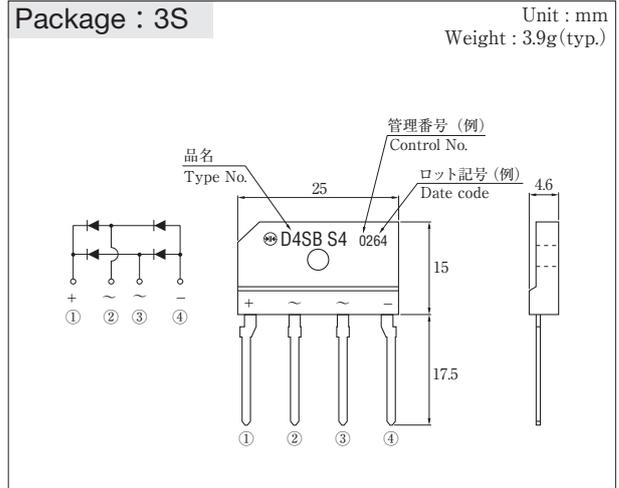
**特長**

- 薄型 SIP パッケージ
- SBD ブリッジ
- 低  $V_F$

**Feature**

- Thin-SIP
- SBD Bridge
- Low  $V_F$

**外観図 OUTLINE**



外形図については新電元 Web サイト又は〈半導体製品一覧表〉をご参照下さい。捺印表示については捺印仕様をご確認下さい。  
For details of outline dimensions, refer to our web site or the Semiconductor Short Form Catalog. As for the marking, refer to the specification "Marking, Terminal Connection."

**定格表 RATINGS**

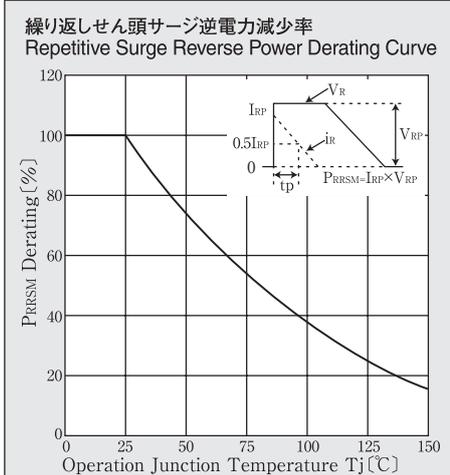
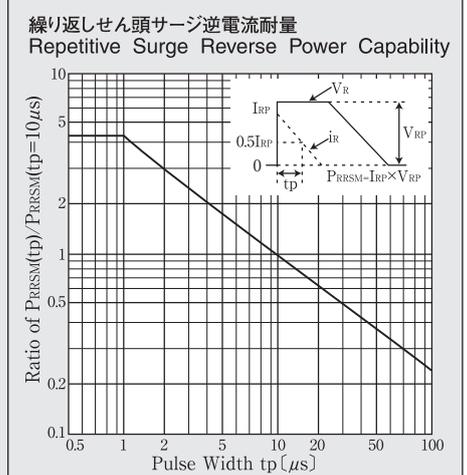
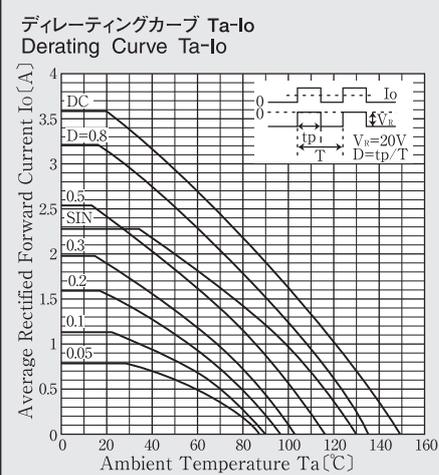
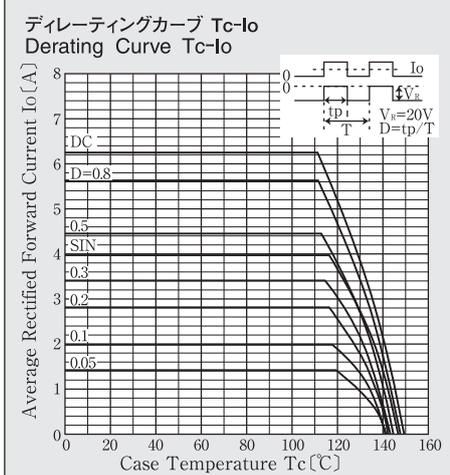
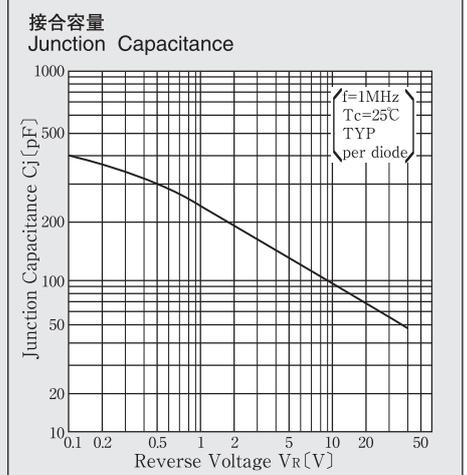
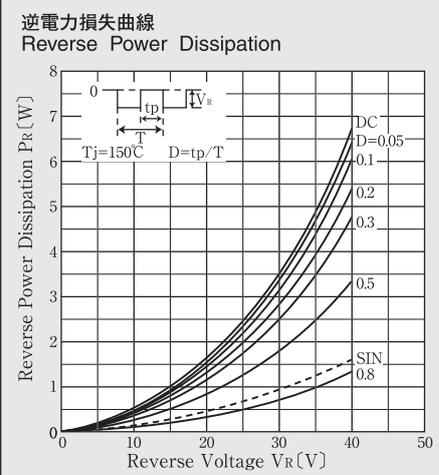
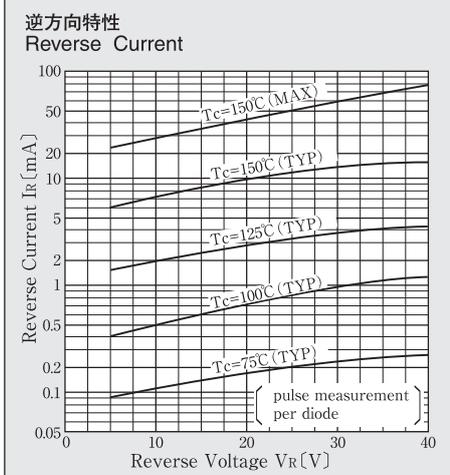
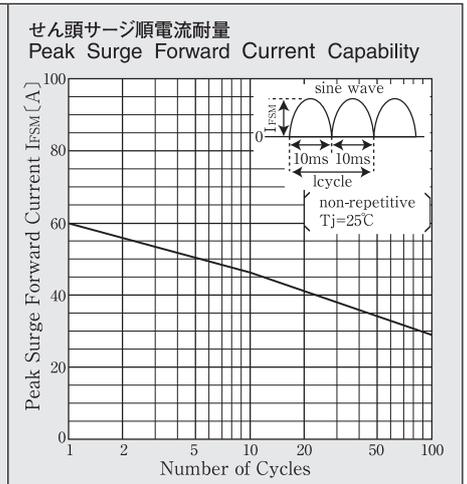
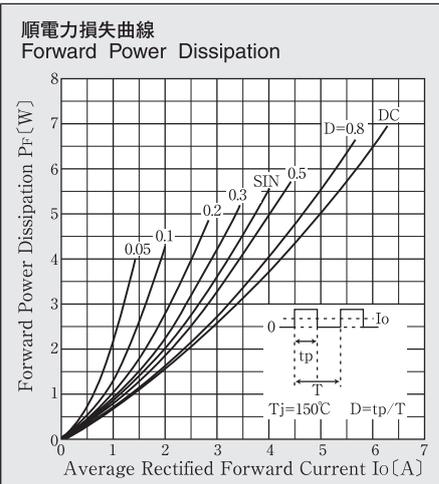
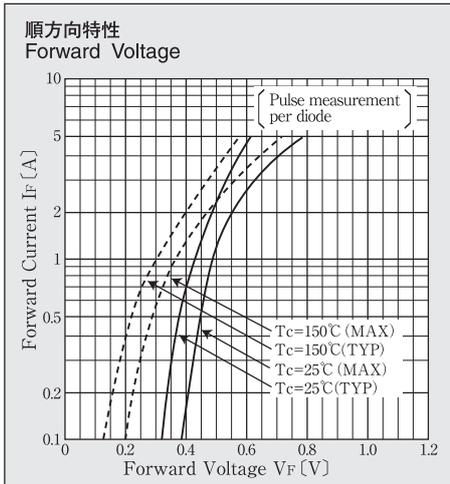
●絶対最大定格 Absolute Maximum Ratings (指定のない場合  $T_C=25^\circ\text{C}$  / unless otherwise specified)

項目 Item	記号 Symbol	条件 Conditions	品名 Type No.	D4SBS4	単位 Unit	
保存温度 Storage Temperature	$T_{stg}$			-55~150	$^\circ\text{C}$	
接合部温度 Operation Junction Temperature	$T_j$			150	$^\circ\text{C}$	
せん頭逆電圧 Maximum Reverse Voltage	$V_{RM}$			40	V	
繰り返しせん頭サージ逆電圧 Repetitive Peak Surge Voltage	$V_{RRSM}$	パルス幅0.5ms, duty 1/40 Pulse width 0.5ms, duty 1/40		45	V	
出力電流 Average Rectified Forward Current	$I_O$	50Hz 正弦波, 抵抗負荷 50Hz sine wave, Resistance load	フィン付き With heatsink	$T_C=116^\circ\text{C}$	4	A
			フィンなし Without heatsink	$T_a=33^\circ\text{C}$	2.3	
せん頭サージ順電流 Peak Surge Forward Current	$I_{FSM}$	50Hz 正弦波, 非繰り返し1サイクルせん頭値, $T_j=25^\circ\text{C}$ 50Hz sine wave, Non-repetitive 1 cycle peak value, $T_j=25^\circ\text{C}$		60	A	
繰り返しせん頭サージ逆電力 Repetitive Peak Surge Reverse Power	$P_{RRSM}$	パルス幅10 $\mu\text{s}$ , 1素子当たり, $T_j=25^\circ\text{C}$ Pulse width 10 $\mu\text{s}$ , per diode, $T_j=25^\circ\text{C}$		160	W	
絶縁耐圧 Dielectric Strength	$V_{dis}$	一括端子・ケース間, AC 1分間印加 Terminals to Case, AC 1 minute		2	kV	
締め付けトルク Mounting Torque	TOR	(推奨値: 0.5 N·m) (Recommended torque: 0.5 N·m)		0.8	N·m	

●電氣的・熱的特性 Electrical Characteristics (指定のない場合  $T_C=25^\circ\text{C}$  / unless otherwise specified)

順電圧 Forward Voltage	$V_F$	$I_F=2\text{A}$ , パルス測定, 1素子当たりの規格値 Pulse measurement, per diode	MAX	0.55	V
逆電流 Reverse Current	$I_R$	$V_R=V_{RM}$ , パルス測定, 1素子当たりの規格値 Pulse measurement, per diode	MAX	2	mA
接合容量 Junction Capacitance	$C_j$	$f=1\text{MHz}$ , $V_R=10\text{V}$ , 1素子当たりの規格値 per diode	TYP	95	pF
熱抵抗 Thermal Resistance	$\theta_{jc}$	接合部・ケース間, フィン付き Junction to Case, With heatsink	MAX	5.5	$^\circ\text{C}/\text{W}$
	$\theta_{jl}$	接合部・リード間, フィンなし Junction to Lead, Without heatsink	MAX	6	
	$\theta_{ja}$	接合部・周囲間, フィンなし Junction to Ambient, Without heatsink	MAX	40	

■特性図 CHARACTERISTIC DIAGRAMS



\* Sine wave は 50Hz で測定しています。  
 \* 50Hz sine wave is used for measurements.  
 \* 半導体製品の特性は一般的にバラツキを持っています。  
 Typical は統計的な実力を表しています。  
 \* Semiconductor products generally have characteristic variation.  
 Typical is a statistical average of the device's ability.